

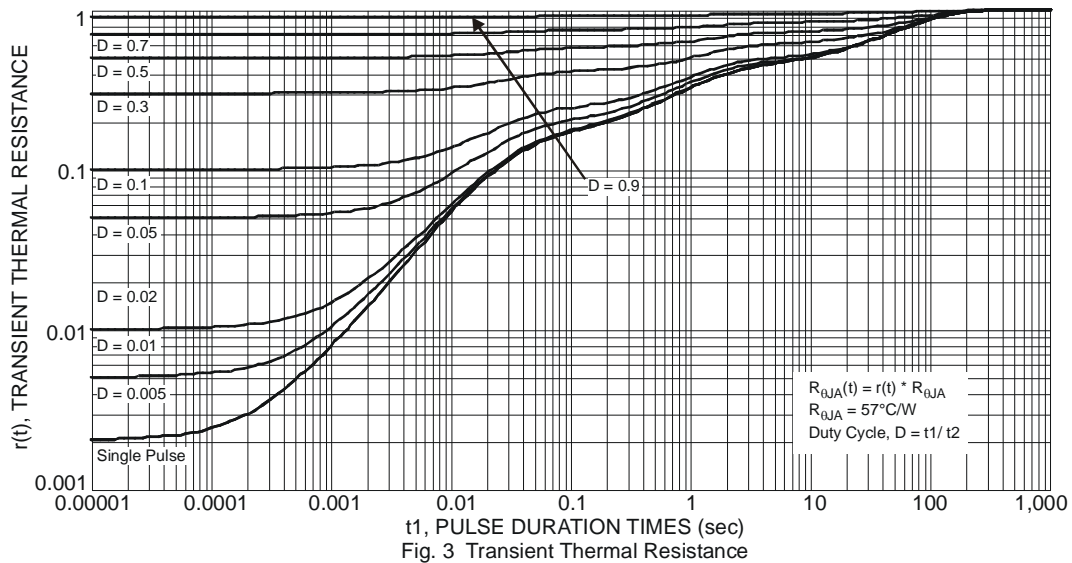
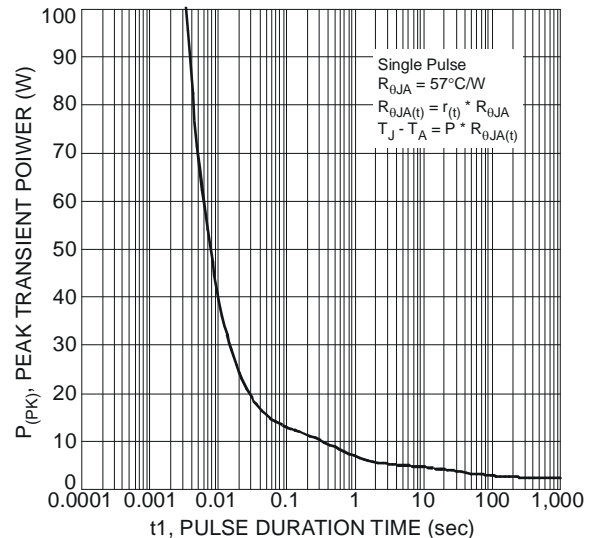
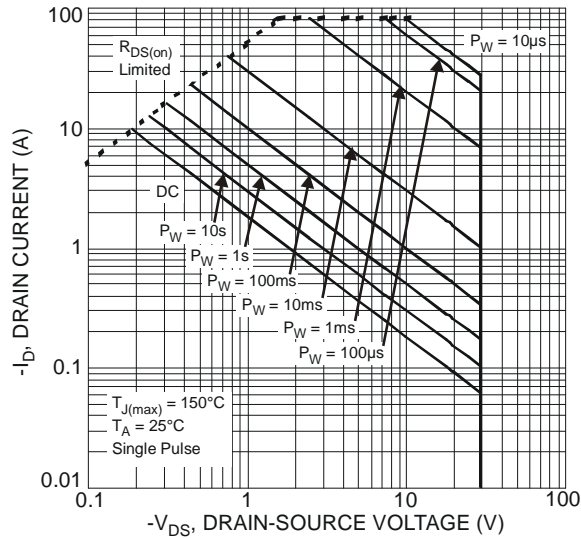
Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-8.6 -7.0	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-11.7 -9.3	A
Continuous Drain Current (Note 7) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-7.1 -5.6	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-9.6 -7.6	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	-80	A
Maximum Continuous Body Diode Forward Current (Note 7)			I _S	-3.0	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		P _D	0.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	140	°C/W
	t < 10s		72	°C/W
Total Power Dissipation (Note 7)		P _D	2.2	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R _{θJA}	57	°C/W
	t < 10s		30	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	7.1	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-1.1	-1.6	-2.1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	12.5	17	mΩ	V _{GS} = -10V, I _D = -10A
		—	18.5	25		V _{GS} = -4.5V, I _D = -10A
Forward Transfer Admittance	Y _{fs}	—	13	—	S	V _{DS} = -15V, I _D = -10A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	2,230	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	328	—		
Reverse Transfer Capacitance	C _{rss}	—	294	—		
Gate Resistance	R _G	—	6.4	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -10V)	Q _g	—	47	—	nC	V _{DS} = -15V, I _D = -10A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	23	—		
Gate-Source Charge	Q _{gs}	—	9.4	—		
Gate-Drain Charge	Q _{gd}	—	5.6	—		
Turn-On Delay Time	t _{D(ON)}	—	10.5	—	nS	V _{GS} = -10V, V _{DS} = -15V, R _G = 6Ω
Turn-On Rise Time	t _R	—	8.5	—		
Turn-Off Delay Time	t _{D(OFF)}	—	90	—		
Turn-Off Fall Time	t _F	—	40	—		

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

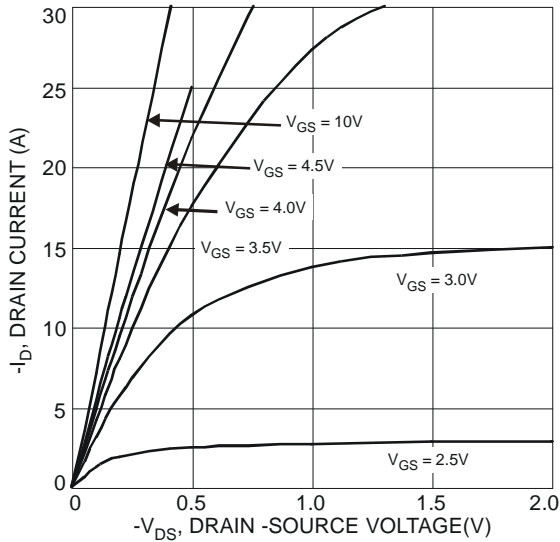


Fig. 4 Typical Output Characteristics

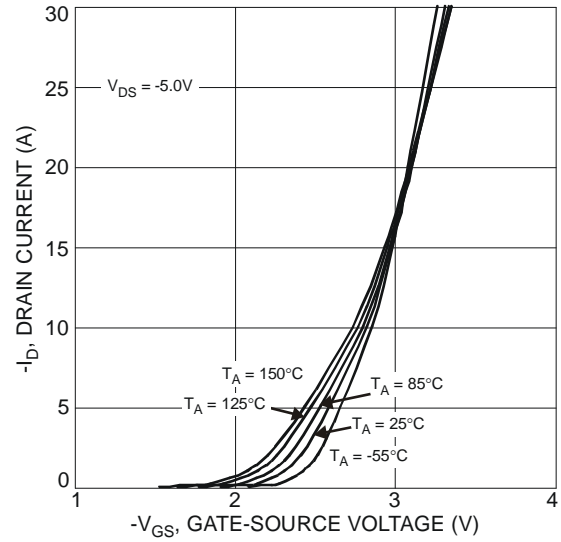


Fig. 5 Typical Transfer Characteristics

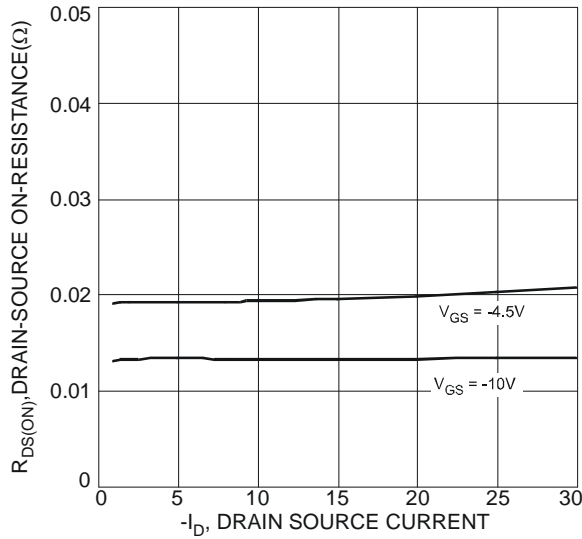


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

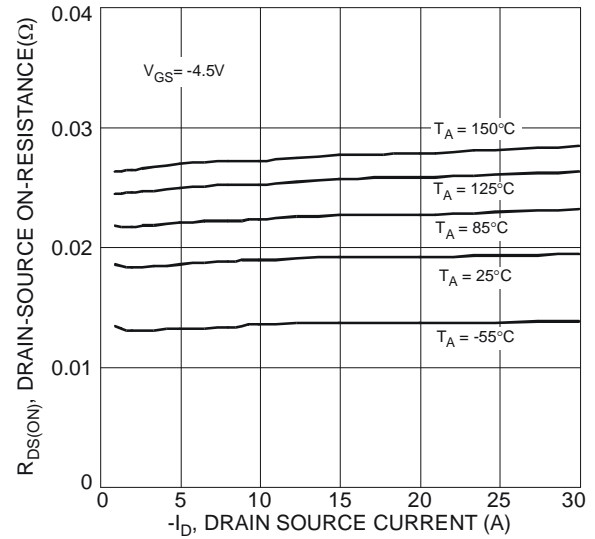


Fig. 7 Typical On-Resistance vs. Drain Current and Temperature

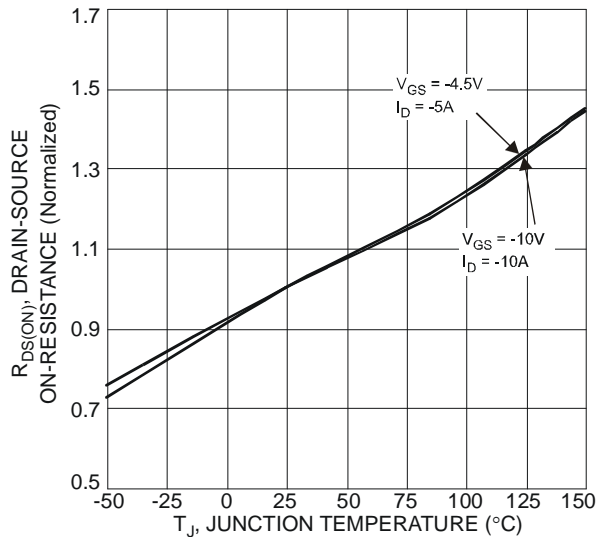


Fig. 8 On-Resistance Variation with Temperature

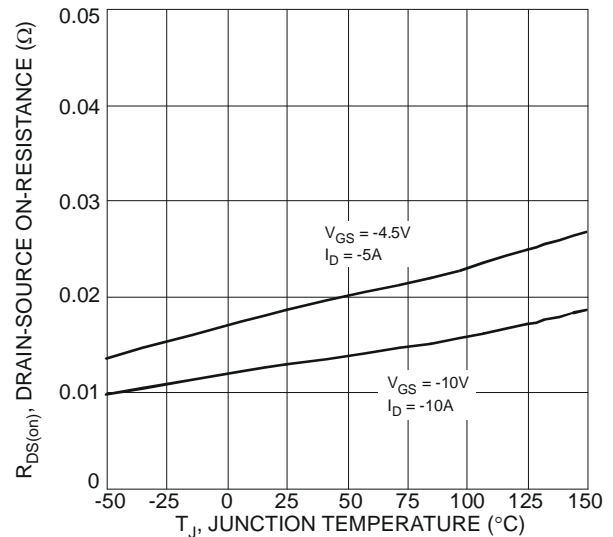


Fig. 9 On-Resistance Variation with Temperature

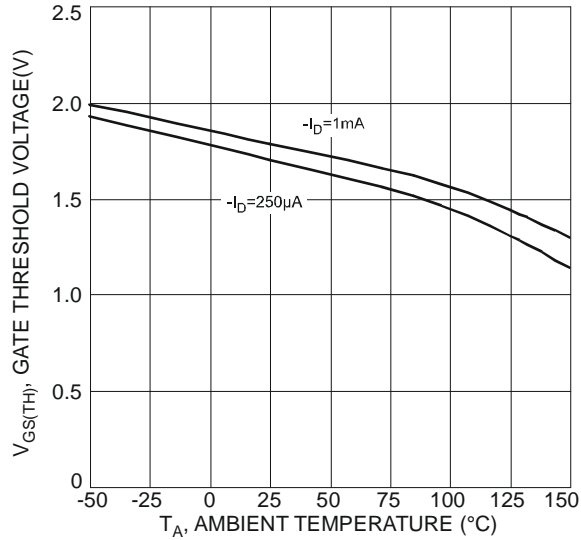


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

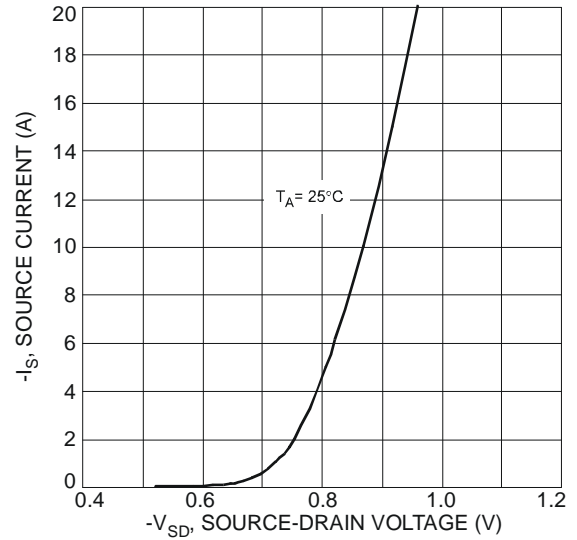


Fig. 11 Diode Forward Voltage vs. Current

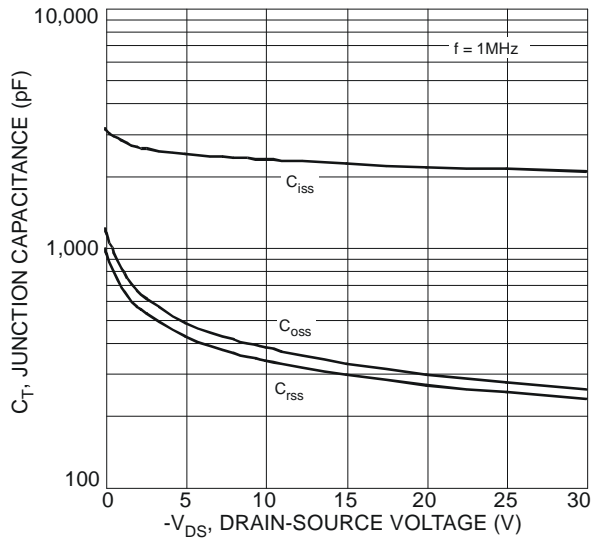


Fig. 12 Typical Junction Capacitance

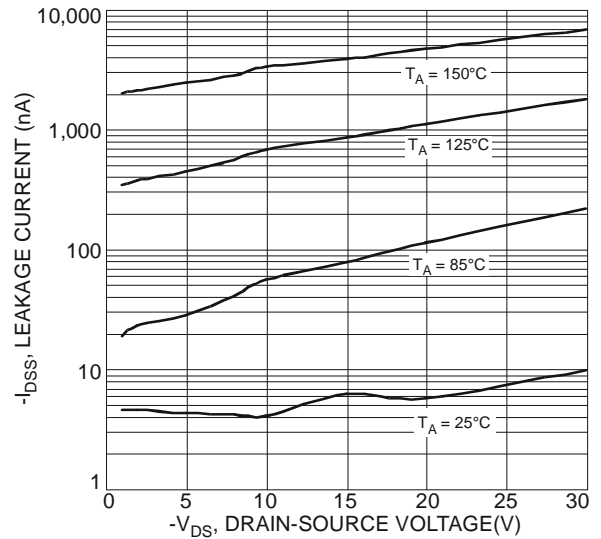


Fig. 13 Typical Drain-Source Leakage Current vs. Voltage

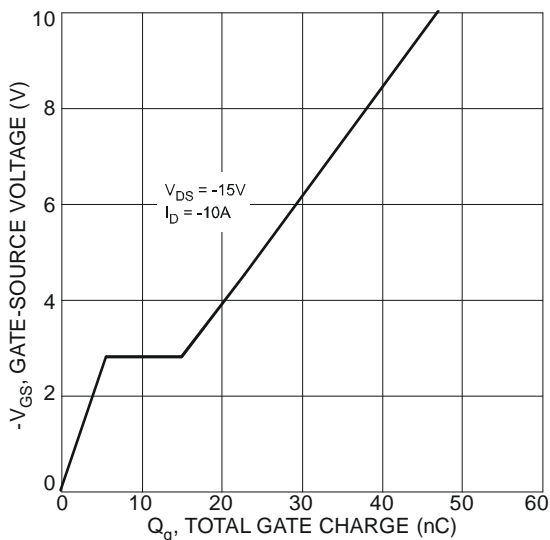
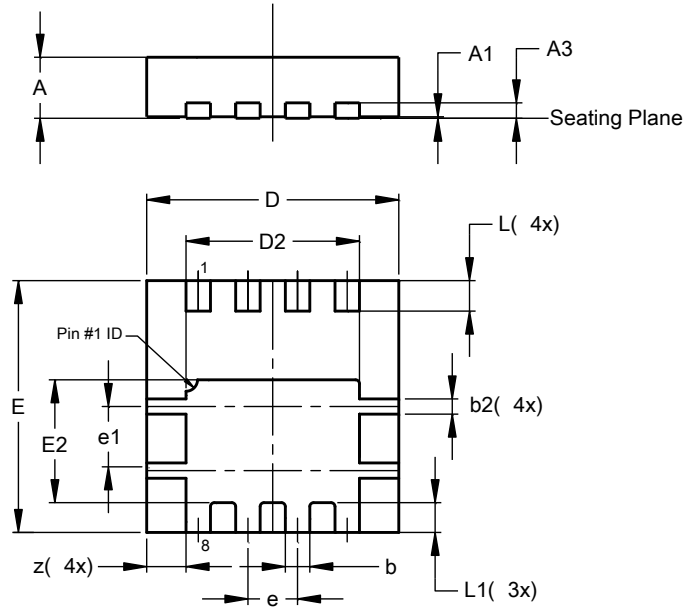


Fig. 14 Gate-Charge Characteristics

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

PowerDI3333-8

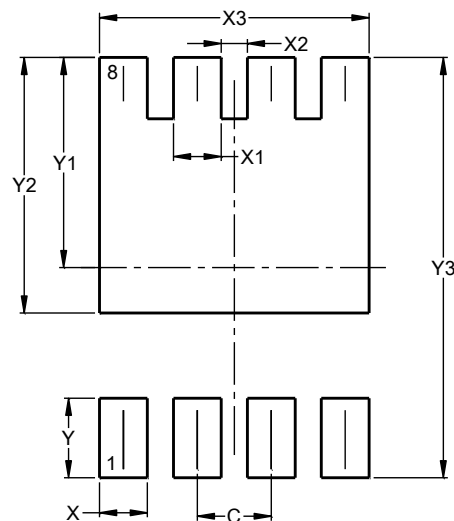


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	—	—	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	—	—	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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